

Description

The QR0502P6 is an uni-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The QR0502P6 has an ultra-low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 25\text{kV}$ air and $\pm 20\text{kV}$ contact discharge. It is assembled into an ultra-small 1.6x1.0x0.75mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make QR0502P6 an ideal choice to protect cell phone, digital video interfaces and other high speed ports.

Features

- Small package: 1.6x1.0x0.75mm
- Ultra low capacitance: 0.6pF typical
- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- 6-pin leadless package
- Protects two lines
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 25\text{kV}$
 - Contact discharge: $\pm 20\text{kV}$
 - IEC61000-4-5 (Lightning) 5A (8/20 μs)
- RoHS Compliant

Mechanical Characteristics

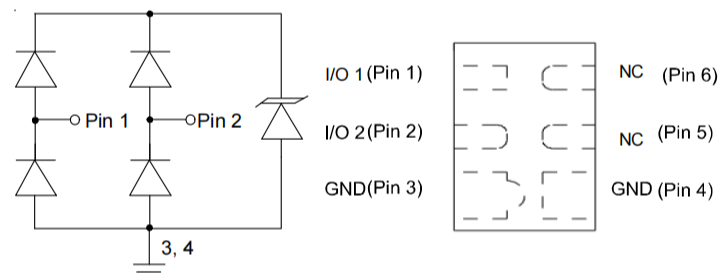
- Package: DFN1610-6
- Case Material: "Green" Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

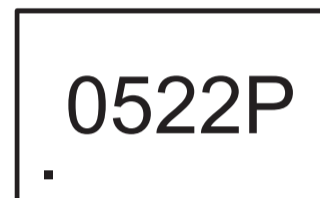
- Cellular Handsets and Accessories
- USB Ports
- Video Interface
- MDDI Ports



DFN1610-6



Circuit diagram



0522P= Device code

Dot denotes Pin1

Marking (Top View)

Ordering Information

Part Number	Packaging	Reel Size
QR0502P6	3000/Tape & Reel	7 inch

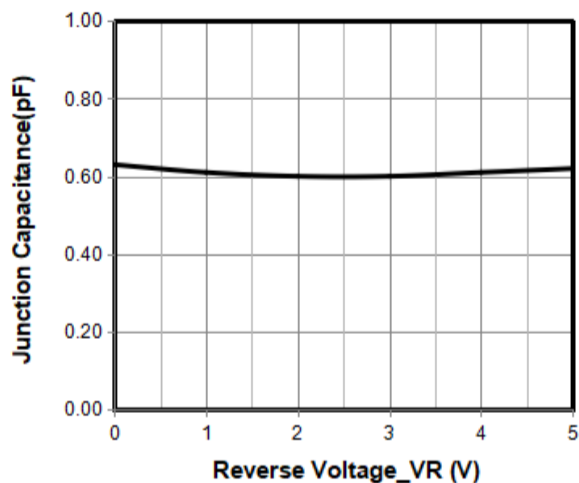
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	Ppk	75	W
Peak Pulse Current (8/20 μs)	I _{PP}	5	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	± 25 ± 20	kV
Operating Temperature Range	T _J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T _{stg}	-55 to +150	$^{\circ}\text{C}$

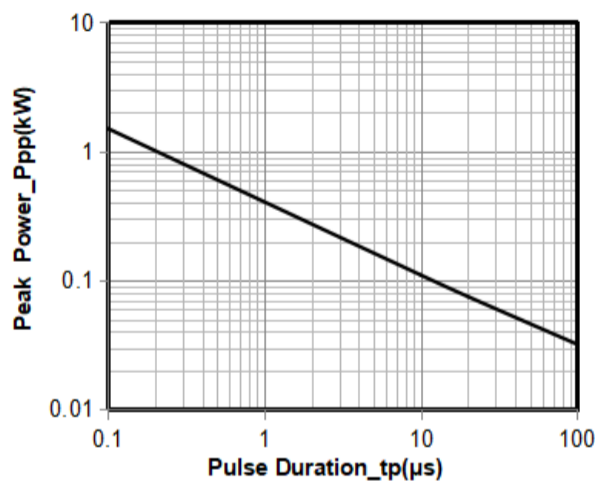
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			5	V	
Breakdown Voltage	V _{BR}	6			V	I _T = 1mA
Reverse Leakage Current	I _R			0.5	μA	V _{RWM} = 5V
Clamping Voltage	V _C			10	V	I _{PP} = 1A (8 x 20 μs pulse), any I/O pin to ground
Clamping Voltage	V _C			15	V	I _{PP} = 5A (8 x 20 μs pulse), any I/O pin to ground
Junction Capacitance	C _J		0.3	0.4	pF	V _R = 0V, f = 1MHz, between I/O pins
Junction Capacitance	C _J			0.8	pF	V _R = 0V, f = 1MHz, any I/O pin to ground

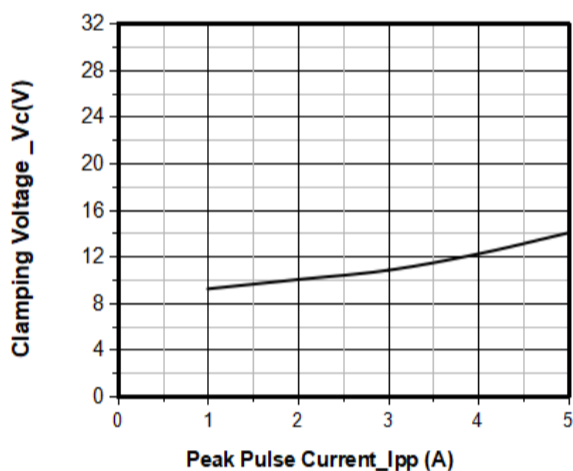
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



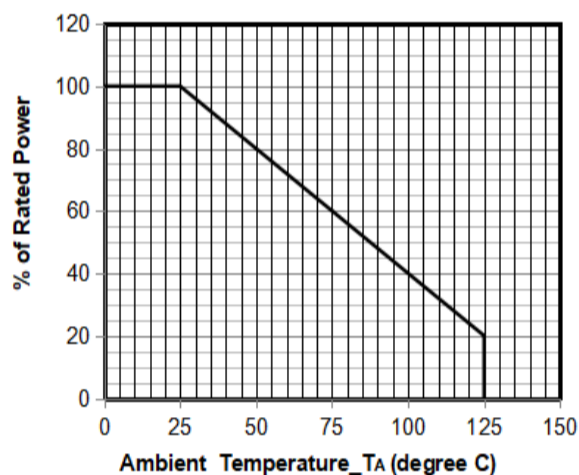
Junction Capacitance vs. Reverse Voltage



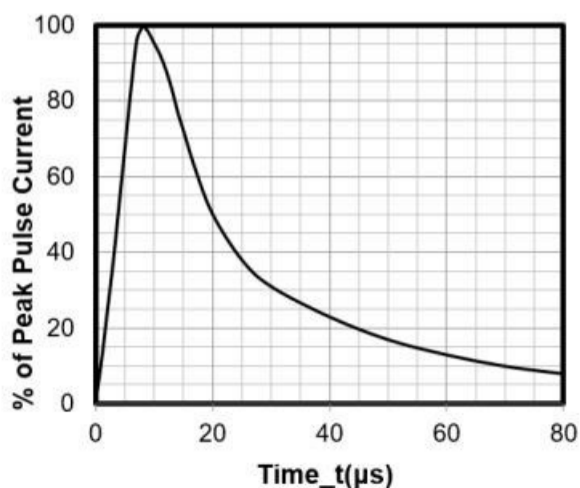
Peak Pulse Power vs. Pulse Time



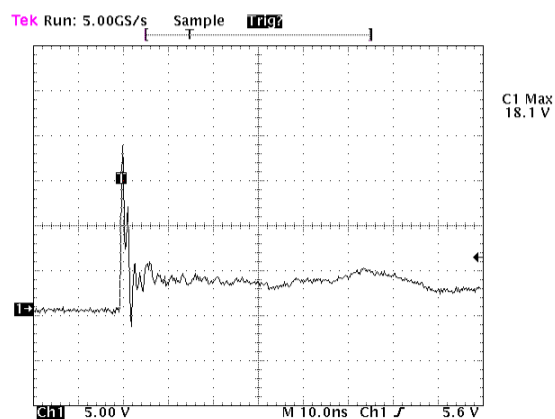
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

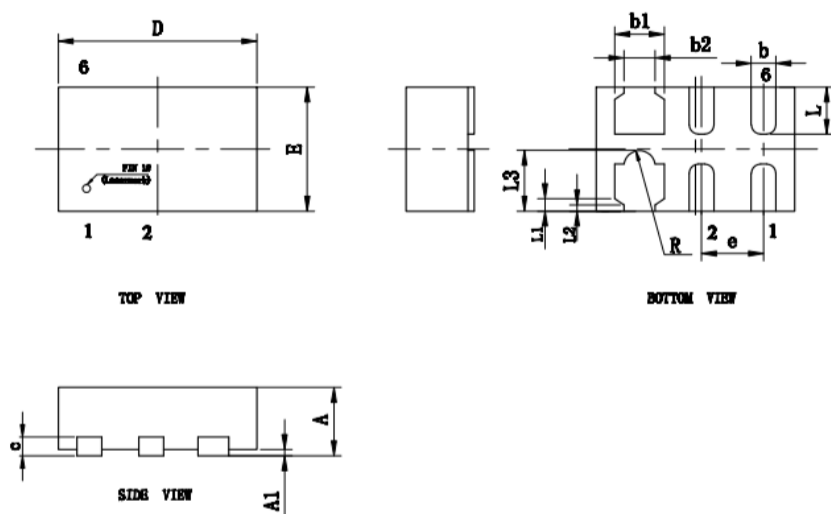


Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

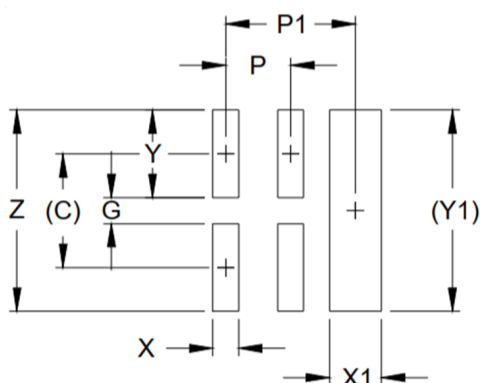
8 kV Contact per IEC61000-4-2

DFN1610-6 Package Outline Drawing



SYM	MILLIMETERS		
	MIN	NOM	MAX
A	0.50	0.55	0.60
A1	--	0.02	0.05
b	0.15	0.20	0.25
b1	0.35	0.40	0.45
b2	0.20	0.25	0.30
c	0.10	0.15	0.20
D	1.55	1.60	1.65
E	0.95	1.00	1.05
e	0.50BSC		
L	0.33	0.38	0.43
L1	0.100REF		
L2	0.05REF		
L3	0.49REF		
R	0.08	0.13	0.18

Suggested Land Pattern



DIM	DIMENSIONS	
	INCHES	MILLIMETERS
C	(.034)	(0.87)
G	.007	0.19
P	.020	0.50
P1	.039	1.00
X	.008	0.20
X1	.016	0.40
Y	.027	0.68
Y1	(.061)	(1.55)
Z	.061	1.55

Contact Information

QingYan Microelectronics Inc.

Website: www.qingyanmicroelectronics.com

Email: qingyan@qingyanmicroelectronics.com

Phone: +86 (0519) 8338 8003